POSTER PRESENTATIONS			
MONDAY	18-Sep-23	13:00-15:20	
Popek	Piotr	Peierls Distortion in Ultra-Confined GeTe and Sb Thin Films	P 1
Stepanov	Roman	Pressure-induced reconfiguration of the van der Waals gap in two-dimensional chalcogenides: an ab-initio study	P 2
De Simone	Sara	Structural and vibrational properties of Ge-rich GexSb2Te5 layers grown on Si(100)	P 3
Tan	Jieling	Synthesis and characterizations of Ge-Sb-O thin films	P 4
Wang	Xiaozhe	Spin glass behavior in amorphous Cr2Ge2Te6 phase-change alloy	P 5
Sun	Suyang	Structural and optical properties of As2Te3	P 6
Wang	Yinli	Resistance change as a function of strain in Cr2Ge2Te6 amorphous thin film on polyimide substrate	P 7
Kim	Mihyeon	Phase change behaviors in Cr-Mn-Te thin film	P 8
Lim	Hyeonwook	Advanced interfacial phase change material: Controlling intrinsic thermal barrier with doping transition metal	P 9
Mai	Xianliang	Ge-free OTS material with weak segregation	P 10
Wredh	Simon	Multi-level Optical Switching by Amorphization in Single- and Multi- Phase Change Material Structures	P 11
Prili	Simone	Interface development in In-based PCM heterostructure	P 12
Yadav	Aakash	Investigating the polarity dependence of multi-level cell operation in conventional mushroom phase change memory cells	P 13
Jakobs	Stefan	Structural Characterization of Ge-rich Ge-Sb-Te films on Silicon and Polyimide Substrates using X-ray Diffraction	P 14
Park	Jaemin	Understanding of Ta doping effect into the Sb2Te3 for high-speed phase change memory	P 15
Pady	Joseph	Flexible Electronics Applications of Ge-rich and Selenium Substituted Phase-change Materials in Non-volatile Memories	P 16
Diaz Fattorini	Adriano	Improved thermal stability of chalcogenide (Ge-Sb-Te) based heterostructures	P 17
Grisolia	Jérémie	AC dynamic conductivity of GGST cells in the RESET state revealed by impedance spectroscopy	P 18
Karam	Lara	Chalcogenide materials integration in silicon photonics for on-chip stochastic computing	P 19
Song	Junchao	Enhancing the performance of integrated phase-change photonic memories using plasmonic nanoantennas	P 20
Humphreys	Euan	Investigation of diffusion effects in tuneable phase-change extraordinary optical transmission bandpass filters	P 21
Adanan	Nur Qalishah	Continuously Tuneable optical states of highly-ordered Sb2Te3	P 22
Baratella	Dario	Unraveling the crystallization kinetics of Ge-rich GexTe phase change alloys with a machine-learned interatomic potential	P 23
Hur	Namwook	Vertically Integrated Three-Dimensional Phase-Change Memory with Heater-All-Around Configuration	P 24
Yoon	Sohui	Cryogenic Operation of Phase Change Memory	P 25
Antonelli	Renzo	Programming Characteristics in Innovative 1S1R "DPSA" Wall PCM + OTS Devices	P 26
Petrucci	Christian	Epitaxial growth and characterization of TiTe2 and PCMs/TiTe2 heterostructures	
			P 27
		Section 200 Conference of the	P 27
TUESDAY	19-Sep-23	12:45-15:00	P 27
TUESDAY Ritarossi	19-Sep-23 Simone		P 27
		12:45-15:00	
Ritarossi	Simone	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures	P 28
Ritarossi Righi Riva	Simone Flavia	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy	P 28
Ritarossi Righi Riva Mouawad	Simone Flavia Oussama	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?	P 28 P 29 P 30
Ritarossi Righi Riva Mouawad Zhou Yusuke	Simone Flavia Oussama Wen	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display	P 28 P 29 P 30 P 31
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tominaga	Simone Flavia Oussama Wen Miyaguchi	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (IPCM) deposited at room temperature -II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer	P 28 P 29 P 30 P 31 P 32
Ritarossi Righi Riva Mouawad Zhou Yusuke	Simone Flavia Oussama Wen Miyaguchi Miyaguchi	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (iPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer  Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer	P 28 P 29 P 30 P 31 P 32 P 33
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Teminoge Kang	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Junji Shin Young	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature - II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe	P 28 P 29 P 30 P 31 P 32 P 33 P 34
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tominoga Kang Chen	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Jerriyi Shin Young Yuhan	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer  Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer  Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tominoge Kang Chen Schenk	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tenninge Kang Chen Schenk Manivannan	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36
Ritarossi Righi Riva Mouawad Zhou Yusuke Terninaga Kang Chen Schenk Manivannan	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Seniyi Shin Young Yuhan Florian M Anbarasu Yi	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (IPCM) deposited at room temperature -II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe  Solution-processed phase-change memory from molecular telluride inks  Sub-threshold current evolution in GeTe phase change memory device  Phase-change Chromium Nitride	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Teminage Kang Chen Schenk Manivannan Shuang Laprais Ravsher	Simone Flavia Oussama Wen Miyaguchi	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride  Optical switch of Sb2S3 for tunable nanophotonics Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tominoga Kang Chen Schenk Manivannan Shuang Laprais	Simone Flavia Oussama Wen Miyaguchi Miyaguchi senji Shin Young Yuhan Florian M Anbarasu Yi Capucine	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe  Solution-processed phase-change memory from molecular telluride inks  Sub-threshold current evolution in GeTe phase change memory device  Phase-change Chromium Nitride  Optical switch of Sb2S3 for tunable nanophotonics	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Teminage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer  Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer  Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe  Solution-processed phase-change memory from molecular telluride inks  Sub-threshold current evolution in GeTe phase change memory device  Phase-change Chromium Nitride  Optical switch of Sb2S3 for tunable nanophotonics  Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tominage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display interfacial phase-change memory (iPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer interfacial phase-change memory (iPCM) deposited at room temperature-IA proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride  Optical switch of Sb2S3 for tunable nanophotonics  Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge2Sb2Te5  Crystallization dynamics probed by transient resistance in phase change memory cells	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Tominage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer  Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer  Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe  Solution-processed phase-change memory from molecular telluride inks  Sub-threshold current evolution in GeTe phase change memory device  Phase-change Chromium Nitride  Optical switch of Sb253 for tunable nanophotonics  Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters  Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge25b2Te5  Crystallization dynamics probed by transient resistance in phase change memory cells  Thermal recrystallization of Ge-rich GeSbTe based phase-change memory cells revealed by TEM	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Tenninge Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-IA proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride  Optical switch of Sb253 for tunable nanophotonics  Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters  Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge25b2Te5  Crystallization dynamics probed by transient resistance in phase change memory cells  Thermal recrystallization of Ge-rich GeSbTe based phase-change memory cells revealed by TEM  Temperature induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Tenninge Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer  Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer  Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe  Solution-processed phase-change memory from molecular telluride inks  Sub-threshold current evolution in GeTe phase change memory device  Phase-change Chromium Nitride  Optical switch of Sb2S3 for tunable nanophotonics  Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters  Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge2Sb2Te5  Crystallization dynamics probed by transient resistance in phase change memory cells  Thermal recrystallization of Ge-rich GeSbTe based phase-change memory cells revealed by TEM  Temperature induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature  Charge Trapping, Resistance Drift and Electronic Transport in Phase Change Memory Devices	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Tominage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem Bychkov	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin Eugene	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications? Anisotropic GaTe thin-film device for reflective display interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride Optical switch of Sb253 for tunable nanophotonics Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge25b2TeS Crystallization dynamics probed by transient resistance in phase change memory cells Thermal recrystallization of Ge-rich GeSbTe based phase-change memory cells revealed by TEM Temperature induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature Charge Trapping, Resistance Drift and Electronic Transport in Phase Change Memory Devices Atomic Structure and Dynamics of Unusual and Wide Gap Phase-Change Chalcogenides	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45 P 46
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Yusuke Yusuke Horinoge Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem Bychkov Berguiga	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin Eugene Lotfi	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications? Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (iPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride Optical switch of Sb2S3 for tunable nanophotonics Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge2Sb2Te5 Crystallization dynamics probed by transient resistance in phase change memory cells revealed by TEM Temperature induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature Charge Trapping, Resistance Drift and Electronic Transport in Phase Change Memory Devices Atomic Structure and Dynamics of Unusual and Wide Gap	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45 P 46 P 47
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Tominege Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem Bychkov Berguiga Kwon	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Jeorija Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin Eugene Lotfi Yongwoo	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (IPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride Optical switch of Sb2S3 for tunable nanophotonics Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge2Sb2Te5 Crystallization dynamics probed by transient resistance in phase change memory cells Thermal recrystallization of Ge-rich GeSbTe based phase-change memory cells revealed by TEM Temperature Induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature Charge Trapping, Resistance Drift and Electronic Transport in Phas	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45 P 46 P 47 P 48
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Tominage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem Bychkov Berguiga Kwon Daoudi	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin Eugene Lotfi Yongwoo Oumaima	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (iPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change defer with Enhanced Weight Modulation for artificial synapses Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride  Optical switch of Sb253 for tunable nanophotonics Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters  Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge25b2TeS  Crystallization dynamics probed by transient resistance in phase change memory cells  Thermal recrystallization of Ge-rich Ge5DTe based phase-change memory cells revealed by TEM  Temperature Induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature  Charge Trapping, Resistance Drift and Electronic Transport in Phase Change Memory Devices  Atomic Structure and Dynam	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45 P 46 P 47 P 48 P 49
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Toninage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem Bychkov Berguiga Kwon Daoudi	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin Eugene Lotfi Yongwoo Oumaima Akasah	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures  Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display  Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer  Interfacial phase-change memory (IPCM) deposited at room temperature-II Superlattice formation using two-step annealing from amorphous multilayer  Silicon-doped GeTe with Enhanced Weight Modulation for artificial synapses  Atomistic study of the configurational entropy of supercooled liquid GeTe  Solution-processed phase-change memory from molecular telluride inks  Sub-threshold current evolution in GeTe phase change memory device  Phase-change Chromium Nitride  Optical switch of Sb253 for tunable nanophotonics  Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters  Photoinduced Ultrafast Dynamics of Local Correlated Structure in GeZSb2TeS  Crystallization dynamics probed by transient resistance in phase change memory cells  Temperature induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature  Change Trapping, Resistance Drift and Electronic Transport in Phase Change Memory Devices  Atomic Structure and Dynamics of Unusual and Wide Gap Phase-Change Chalcogenides  Perfect absorption and ultimate phase sensitivity in optical sensor by using multi-level phase state of GeSbTe  Analysis of Pulse Shape Dependence in Phase Change Memory Switching Using Fully Transient Device Simulation  Encapsulation Effects on Ge-rich GeSbTe at High Temperature  Temperature-dependent Hermal-conductivity evolution of 14 depend Ge-rich GeSbTe using Roman	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45 P 46 P 47 P 48 P 49 P 50 P 51
Ritarossi Righi Riva Mouawad Zhou Yusuke Yusuke Yusuke Tominage Kang Chen Schenk Manivannan Shuang Laprais Ravsher Jiang Li Ordan Ran Voss Kashem Bychkov Berguiga Kwon Daoudi	Simone Flavia Oussama Wen Miyaguchi Miyaguchi Shin Young Yuhan Florian M Anbarasu Yi Capucine Taras Yuyu Xian-Bin Efrat Sijia Lennart Md Tashfiq Bin Eugene Lotfi Yongwoo Oumaima	12:45-15:00  Confinement Effects on the Structure of Thin Layers of Amorphous Phase-Change Materials inside Heterostructures Interplay between structural and electronic properties in layered GeTe-rich Ge-Sb-Te stabilized by epitaxy  GeSe-GeTe pseudo-binary line: an opportunity for embedded memory applications?  Anisotropic GaTe thin-film device for reflective display Interfacial phase-change memory (iPCM) deposited at room temperature-II Superlattice fabrication on 300 mm Si-wafers using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change memory (iPCM) deposited at room temperature-I A proposal for superlattice formation using two-step annealing from amorphous multilayer Interfacial phase-change defer with Enhanced Weight Modulation for artificial synapses Atomistic study of the configurational entropy of supercooled liquid GeTe Solution-processed phase-change memory from molecular telluride inks Sub-threshold current evolution in GeTe phase change memory device Phase-change Chromium Nitride  Optical switch of Sb253 for tunable nanophotonics Evidence of Heat-Assisted Atomic Migration in GeSe Self-Selecting Memory Operated at High Current Density  Reconfigurable Spoof Surface Plasmon Polariton Microwave Filters  Photoinduced Ultrafast Dynamics of Local Correlated Structure in Ge25b2TeS  Crystallization dynamics probed by transient resistance in phase change memory cells  Thermal recrystallization of Ge-rich Ge5DTe based phase-change memory cells revealed by TEM  Temperature Induced volume change in GeTe-Sb2Te3 heterostructures below the crystallization temperature  Charge Trapping, Resistance Drift and Electronic Transport in Phase Change Memory Devices  Atomic Structure and Dynam	P 28 P 29 P 30 P 31 P 32 P 33 P 34 P 35 P 36 P 37 P 38 P 39 P 40 P 41 P 42 P 43 P 44 P 45 P 46 P 47 P 48 P 49